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5 nm CMOS Production Technology Platform featuring full-fledged EUV, and High Mobility Channel FinFETs with Densest 0.021 μm^2 SRAM Cells for Mobile SoC and High Performance Computing Applications (Late News)

Industry-leading 5 nm CMOS technology features, for the first time, full-fledged EUV, and high mobility channel finFETs, offering ~1.84x logic density, 15% speed gain or 30% power reduction over 7 nm. This true 5 nm technology successfully passed qualification with high yield, and targets for mass production in 1H 2020.

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